

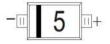
RB751S-40

Schottky barrier Diode

FEATURES

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

MARKING: 5



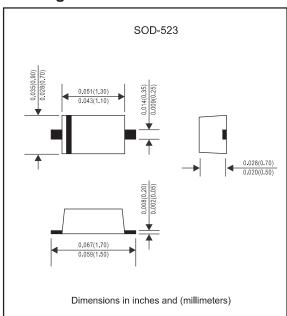








Package outline



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25℃

Parameter	Symbol	Limit	Unit
Peak reverse voltage	V _{RM}	40	V
DC reverse voltage	V _R	40	V
Mean rectifying current	lo	30	mA
Non-repetitive Peak Forward Surge Current@t=8.3ms	I _{FSM}	200	mA
Power dissipation	P _D	150	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	667	°C/W
Operating Junction Temperature Range	T _j	-40 ~ +125	°C
Storage Temperature Range	T _{stg}	-55 ~ + 150	°C

Electrical Ratings @Ta=25℃

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Reverse voltage	V _(BR)	40			٧	I _R =1mA
Forward voltage	V _F	0.20		0.37	>	I _F =1mA
Reverse current	I _R	0.01		0.5	μA	V _R =30V
Capacitance between terminals	Ст	0.5	2	10	pF	V _R =1V,f=1MHZ



Schottky barrier Diode

Typical Characteristics

